AN8480NSB

3-phase full-wave motor driver IC

Overview

The AN8480NSB is a 3-phase full-wave motor driver IC with a reverse rotation brake/short brake changeover function, incorporating a thermal protection circuit with its protection monitor pin.

■ Features

- 3-phase full-wave and snubberless
- FG output
- Current limit
- Reverse rotation prevention
- Thermal protection circuit built-in (with thermal protection monitor pin)

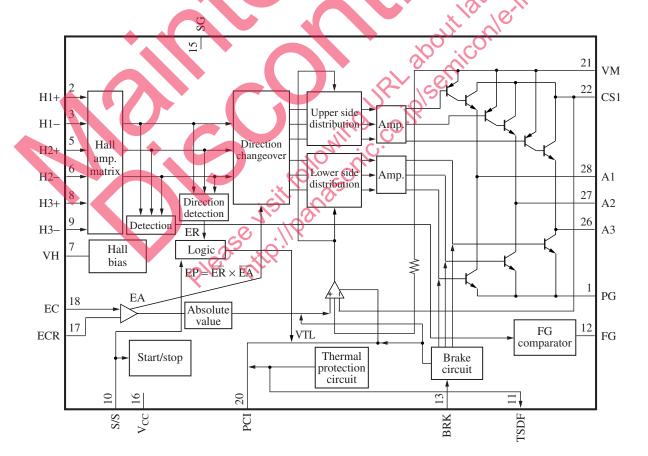
Applications

• Various types of optical disk drive

■ Package

• HSOP042-P-0400D

■ Block Diagram



■ Pin Descriptions

| Pin No. | Symbol | Description | Pin No. | Symbol | Description |
|---------|--------|-----------------------------------|---------|-----------------|---|
| 1 | PG | Power GND pin | 15 | SG | Signal GND pin |
| 2 | H1+ | Hall element-1 positive input pin | 16 | V _{CC} | Supply voltage pin |
| 3 | H1- | Hall element-1 negative input pin | 17 | ECR | Torque command reference input pin |
| 4 | N.C. | N.C. | 18 | EC | Torque command input pin |
| 5 | H2+ | Hall element-2 positive input pin | 19 | N.C. | N.C. |
| 6 | H2- | Hall element-2 negative input pin | 20 | PCI | Current feedback phase compensation pin |
| 7 | VH | Hall bias pin | 21 | VM | Motor supply voltage pin |
| 8 | H3+ | Hall element-3 positive input pin | 22 | CS | Current det. pin 1 |
| 9 | Н3- | Hall element-3 negative input pin | 23 | N.C. | N.C. |
| 10 | SS | Start/stop changeover pin | 24 | N.C. | N.C. |
| 11 | TFLG | Thermal protection monitor pin | 25 | N.C. | N.C. |
| 12 | FG | FG signal output pin | 26 | A3 | Drive output 3 |
| 13 | BRK | Brake mode setting pin | 27 | A2 | Drive output 2 |
| 14 | N.C. | N.C. | 28 | A1 | Drive output 1 |

■ Absolute Maximum Ratings

| Parameter | Symbol | Rating | Unit |
|----------------------------------|-------------------|-------------------------|------|
| Supply voltage | V_{CC} | 7.0 | V |
| | $V_{\rm M}$ | 14.4.01 (17) | |
| Control signal input voltage *4 | V _(n) | 0 to V _{CC} | V |
| Supply current | I_{CC} | 300 | mA |
| Output current *3 | I _{O(n)} | .±1,200 | mA |
| Hall bias current | I_{HB} | | mA |
| Power dissipation *2 | P_{D} | 10 ¹ ic. 667 | mW |
| Operating ambient temperature *1 | T _{opr} | -20 to +70 | °C |
| Storage temperature *1 | T _{stg} | −55 to +150 | °C |

Note) Do not apply external currents or voltages to any pins not specifically mentioned.

For circuit currents, '+' denotes current flowing into the IC, and '-' denotes current flowing out of the IC.

■ Recommended Operating Range

| Parameter | Symbol | Range | Unit |
|----------------|-------------|-------------|------|
| Supply voltage | V_{CC} | 4.25 to 5.5 | V |
| | $V_{\rm M}$ | 4.5 to 14 | |

^{*1:} Except for the operating ambient temperature and storage temperature, all ratings are for $T_a = 25$ °C.

^{*2:} For 70°C and IC alone.

^{*3:} n = 1, 22, 26, 27, 28

^{*4:} n = 2, 3, 5, 6, 8, 9, 10, 13, 17, 18

\blacksquare Electrical Characteristics at $T_a = 25^{\circ}C$

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--------------------------------------|--------------------|--|------|------|-----------------|---------|
| Overall | | | | | | |
| Circuit current 1 | I_{CC1} | $V_{CC} = 5 \text{ V}$ in power save mode | | 0 | 0.1 | mA |
| Circuit current 2 | I_{CC2} | $V_{CC} = 5 \text{ V}, I_{O} = 0 \text{ mA}$ | 1 | 8 | 16 | mA |
| Start/stop | | | • | | | |
| Start voltage | V _{START} | Voltage with which a circuit operates at V_{CC} = 5 V and L \rightarrow H | 2.7 | | | V |
| Stop voltage | V _{STOP} | Voltage with which a circuit becomes off at $V_{CC} = 5 \text{ V}$ and $H \rightarrow L$ | 3 | _ | 0.7 | V |
| Medium voltage | V _{MED} | Voltage with which V_{PCI} becomes 1.55 low at $V_{CC} = 5 \text{ V}$ and $EC = 0 \text{ V}$ | | | 1.75 | V |
| Hall bias | | | | | | |
| Hall bias voltage | V_{HB} | $V_{CC} = 5 \text{ V}, I_{HB} = 20 \text{ mA}$ | 0.7 | 1.2 | 1.6 | V |
| Hall amplifier | | | K | | < | 7. |
| Input bias current | I_{BH} | $V_{CC} = 5 \text{ V}$ | - | 1 | 25/0 | μΑ |
| In-phase input voltage range | V _{HBR} | $V_{CC} = 5 \text{ V}$ | 1.5 | -4 | 4.0 | V |
| Minimum input level | V _{INH} | $V_{CC} = 5 \text{ V}$ | 60 | 160, | 41, | mV[p-p] |
| Torque command | | | a C | O | F., | |
| In-phase input voltage range | EC | $V_{CC} = 5 \text{ V}$ | 0.5 | 40, | 3.9 | V |
| Offset voltage | EC _{OF} | $V_{CC} = 5 \text{ V}$ | -100 | 0 | 100 | mV |
| Dead zone | EC_{DZ} | $V_{CC} = 5 \text{ V}$ | 25 | 75 | 125 | mV |
| Input current | EC _{IN} | $V_{CC} = 5 \text{ V, EC} = ECR = 1.65 \text{ V}$ | -5 | -1 | _ | μΑ |
| Input/output gain | A _{CS} | $V_{CC} = 5 \text{ V}, R_{CS} = 0.5 \Omega$ | 0.75 | 1.0 | 1.25 | A/V |
| Output | • | 0.16/ | | | | |
| High-level output saturation voltage | V _{OH} | $V_{CC} = 5 \text{ V} \cdot I_{O} = -300 \text{ mA}$ | | 0.9 | 1.6 | V |
| Low-level output saturation voltage | V _{OL} | $V_{CC} = 5 \text{ V}, I_0 = 300 \text{ mA}$ | _ | 0.2 | 0.6 | V |
| Torque limit current | I_{TL} | $V_{CC} = 5 \text{ V. } R_{CS} = 0.5 \Omega$ | 400 | 500 | 600 | mA |
| FG V | | all allow | | | | |
| FG output high-level | FG _H | $V_{CC} = 5 \text{ V}, I_{FG} = -0.01 \text{ mA}$ | 3.0 | | V _{CC} | V |
| FG output low-level | $FG_{\mathbf{L}}$ | $V_{CC} = 5 \text{ V}, I_{FG} = 0.01 \text{ mA}$ | _ | _ | 0.5 | V |
| In-phase input voltage range | V _{FGR} | $V_{CC} = 5 \text{ V},$ Input D-range at H2+, H2- | 1.5 | | 3.0 | V |
| FG hysteresis width | H_{FG} | $V_{CC} = 5 \text{ V}$ | 1 | 10 | 20 | mV |
| Brake cirrcuit | | | | | | |
| Short brake model level | V _{SBR} | $V_{CC} = 5 \text{ V}$ | _ | _ | 1.0 | V |
| Reverse rotation brake mode level | V _{RBR} | V _{CC} = 5 V | 3.5 | _ | _ | V |
| Short brake start level | V _{SBRL} | V _{CC} = 5 V, ECR = 1.65 V | 1.65 | 1.74 | _ | V |
| | I_{SBR} | $V_{CC} = 5 \text{ V}$ | 12 | 35 | | mA |

■ Electrical Characteristics at T_a = 25°C (continued)

• Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

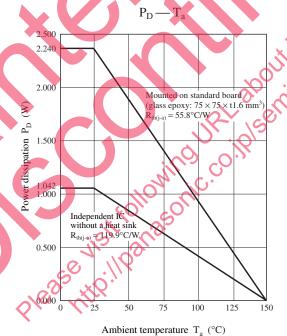
| Parameter Sys | | Conditions | Min | Тур | Max | Unit |
|--|---------------------|--|-----|-----|-----|------|
| Thermal protection | | | | | | |
| Thermal protection operating temperature | T _{SDON} | $V_{CC} = 5 \text{ V}, \Delta EC = 100 \text{ mV}$ | | 160 | | °C |
| Thermal protection hysteresis width | ΔT_{SD} | $V_{CC} = 5 \text{ V}, \Delta EC = 100 \text{ mV}$ | | 45 | _ | °C |
| Thermal protection flag | | | | | | |
| Level at thermal protection = on | V _{TSDON} | $V_{CC} = 5 \text{ V}$ | | | 0.5 | V |
| Level at thermal protection = off | V _{TSDOFF} | $V_{CC} = 5 \text{ V}$ | 3.0 | | _ | V |

■ Usage Notes

Prevent this IC from being line-to-ground fault. (To be concrete, do not short-circuit any of A1 (pin 28), A2 (pin 27) and A3 (pin 26) with VM pin (pin 21).)

■ Application Notes

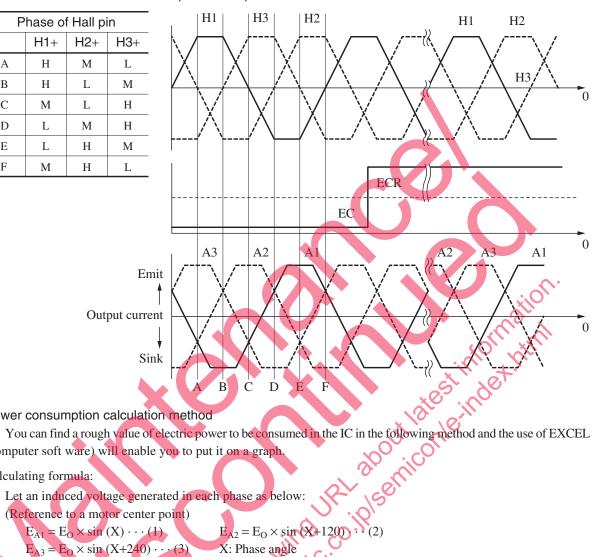
• P_D — T_a curves of HSOP042-P-0400D



Application Notes (continued)

Phase conditions between Hall input and output current

| Phase of Hall pin | | | | | | | | |
|-------------------|---------|---|--------|--|--|--|--|--|
| | H1+ H2+ | | | | | | | |
| A | Н | M | L | | | | | |
| В | Н | L | M | | | | | |
| С | M | L | H H | | | | | |
| D | L | M | | | | | | |
| Е | L | Н | M | | | | | |
| F | M | Н | L | | | | | |



Power consumption calculation method

(computer soft ware) will enable you to put it on a graph.

Calculating formula:

1. Let an induced voltage generated in each phase as below:

$$E_{A1} = E_O \times \sin(X) \cdot \cdots (1)$$
 $E_{A2} = E_O \times \sin(X + 120) \cdot \cdots (2)$

$$E_{A3} = E_0 \times \sin(X + 240) \cdot \cdot \cdot (3)$$
 X: Phase angle

Let a current flowing in each phase as below:

$$I_{A1} = I_O \times \sin(X) \cdot \cdot \cdot (4)$$
 $I_{A2} = I_O \times \sin(X + 120) \cdot \cdot \cdot (5)$
 $I_{A3} = I_O \times \sin(X + 240) \cdot \cdot \cdot (6)$

3. The voltages generated by a wire-wound resistance of a motor are:

$$V_{R1} = I_{A1} \times R \cdot \cdot \cdot (7)$$
 $V_{R2} = I_{A2} \times R \cdot \cdot \cdot (8)$ $V_{R3} = I_{A3} \times R \cdot \cdot \cdot (9)$

4. In each phase, add the voltage generated by an induced voltage and that by a wire-wound resistance.

$$V_{A1}' = (1) + (4)$$
 $V_{A2}' = (2) + (5)$ $V_{A3}' = (3) + (6)$

5. As the lowest voltage in each phase angle must be 0 V, you can get the voltage to be generated in each phase by means of subtracting the lowest voltage from the voltage of the remaining two phases.

$$\begin{aligned} &V_{A1} = V_{A1}' - MIN \ (V_{A1}', V_{A2}', V_{A3}') \cdots (10) \\ &V_{A2} = V_{A2}' - MIN \ (V_{A1}', V_{A2}', V_{A3}') \cdots (11) \\ &V_{A3} = V_{A3}' - MIN \ (V_{A1}', V_{A2}', V_{A3}') \cdots (12) \end{aligned}$$

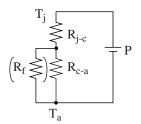
6. Subtract the supply voltage from each phase's voltage found in item 5 and then multiply it by each phase's current, so that you can get the power consumption.

$$P = \sum_{n=1}^{3} (12 - V_{An}) \times I_{An}$$

■ Application Notes (continued)

• Theory of thermal resistance

A chip temperature or the fin temperature can be understood in the same way as Ohm's Law.



T_i: Chip temperature

T_a: Ambient temperature

P: Electric power generated by IC

R_{i-c}: Thermal resistance between a chip and a package

R_{c-a}: Thermal resistance between a package and a surface of a heat sink or free air

R_f: Thermal resistance between a package and surface of a heat sink

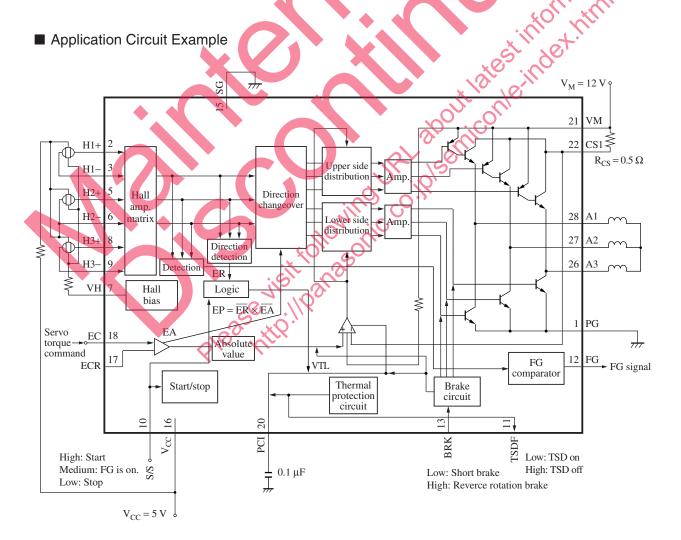
$$T_i = T_a + P \times (R_{i-c} + R_{c-a} // R_f)$$

Make sure that T_j does not exceed 150°C.

If it exceeds 150°C, you can suppress the rise of a chip temperature by adding a heat sink which is equivalent to R_f in the above figure.

$$T_j = T_a + P \times (R_{j-c} + R_{c-a} // R_f)$$

A package surface and the fin are available for a temperature measurement. But the fin part is recommendable for measurement because a package surface measurement does not always promise you a consistent measuring result.



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